

## **Super Barrier Rectifier**

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

#### Major ratings and characteristics

Characteristics	Values	Units
I <sub>F(AV)</sub> Rectangular Waveform	1.0 *	A
$V_{RRM}$	40	V
V <sub>F</sub> @1A, T <sub>J</sub> =75°C	0.42	V, typ
T <sub>J</sub> (operating/storage)	-65 to 125	°C

\*Note: Device monuted on a glass epoxy board,

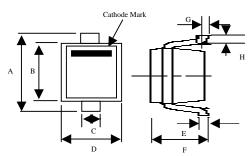
Board size: 50mm x 50m, Land size: 6mm x 6mm

#### **ELECTRICAL:**

- \* Low Forward Voltage Drop
- \* Low Reverse Leakage
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 125°C Operating Junction Temperature

#### MECHANICAL:

\* Molded Plastic SOD-323 package



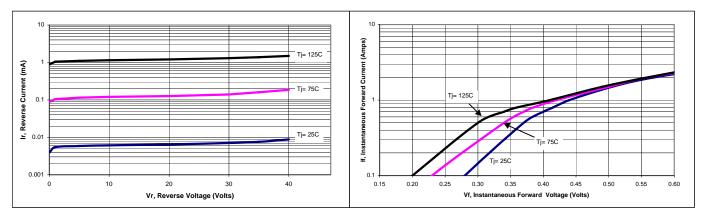
;	SOD-323				
Di	Min	Max			
Α	2.30	2.70			
В	1.60	1.80			
С	0.25	0.40			
D	1.15	1.45			
E	0.10	0.18			
F	0.85	1.05			
G	-	0.10			
Н	0.20	0.40			
All	All Dimensions in mm				

### Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified)

(at 25 C unless otherwise specified)							
	SYMBOL			UNITS			
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V <sub>RM</sub> V <sub>RWM</sub> V <sub>RRM</sub>	40		Volts			
Average Rectified Forward Current (Rated $V_R$ - 20Khz Square Wave) - 50% duty cycle	I <sub>O</sub> <sup>(1)</sup>	1		Amps			
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	18		Amps			
Instantaneous Forward Voltage $I_F = 0.7A$ ; $T_J = 25^{\circ}C$ $I_F = 1A$ ; $T_J = 25^{\circ}C$ $I_F = 0.7A$ ; $T_J = 75^{\circ}C$	V <sub>F</sub>	Typ  0.44 	Max 0.44  0.39	Volts			
Maximum Reverse Current at Rated $V_{RM}$ $T_J = 25^{\circ}C$ $T_J = 75^{\circ}C$	I <sub>R</sub> <sup>(2)</sup>	Тур  	Max 0.2 2	mA mA			
Operating and Storage Junction Temperature	Т,	-65 to +125		°C			

- (1) We recommend that the worst case current be no greater than 80% of the maximum rating of I  $_{
  m O}$
- (2) Pulse width < 300 uS, Duty cycle < 2%

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**Figure 1: Typical Reverse Current** 

Figure 2: Typical Forward Voltage

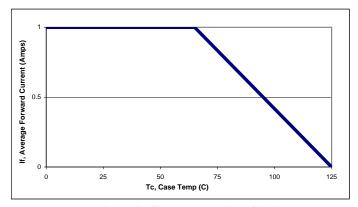
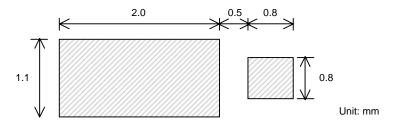


Figure 3: Current Derating, Case\*

#### STANDARD SOLDERING PAD:



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<sup>\*</sup>Device mounted on a 50mm x 50mm glass epoxy board, 50% duty cycle